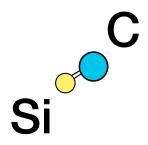
Optical properties of free-standing cubic silicon carbide

Mattias Jansson

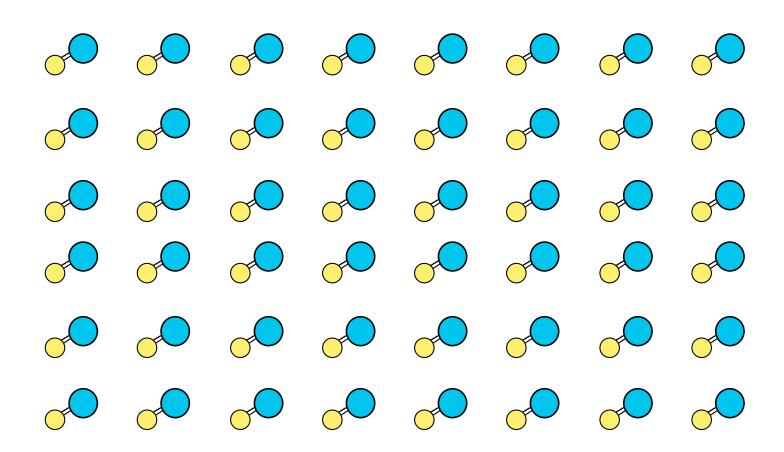




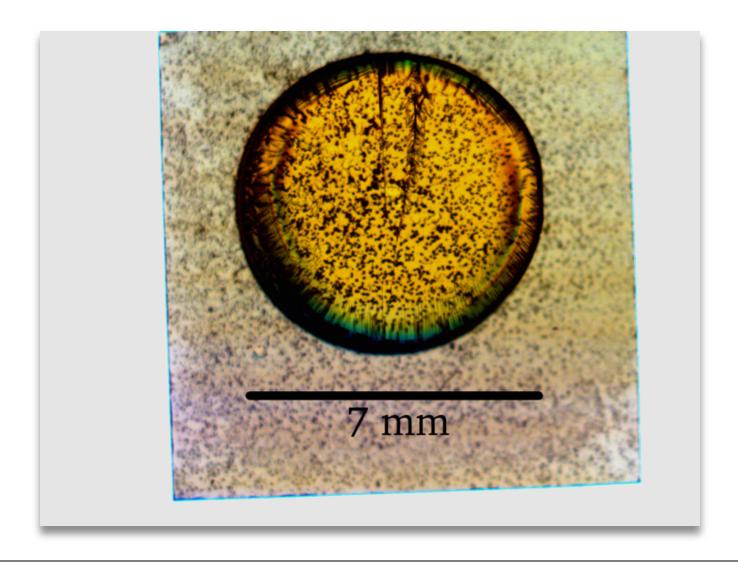






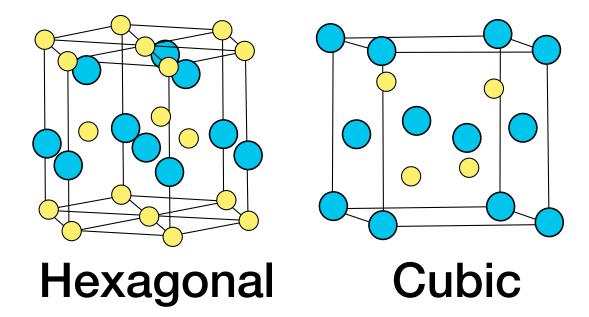






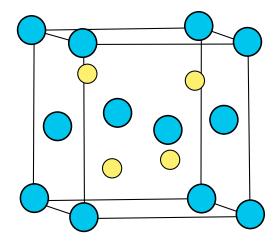


Polytypes - atomic arrangements





Polytypes - atomic arrangements

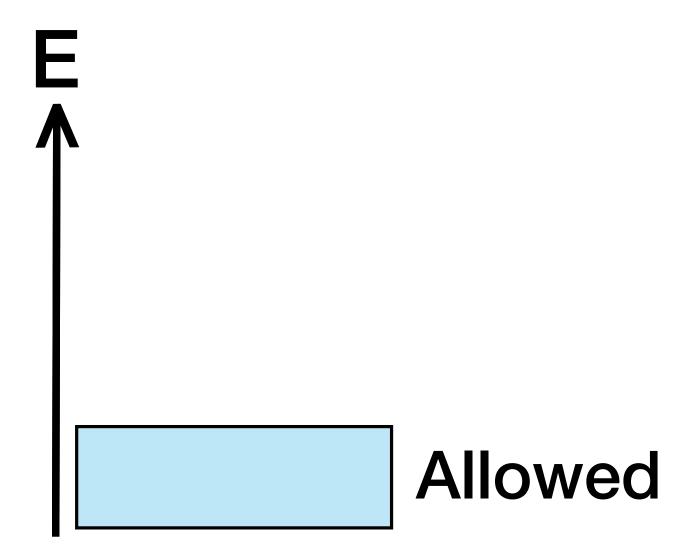


Cubic 3C-SiC

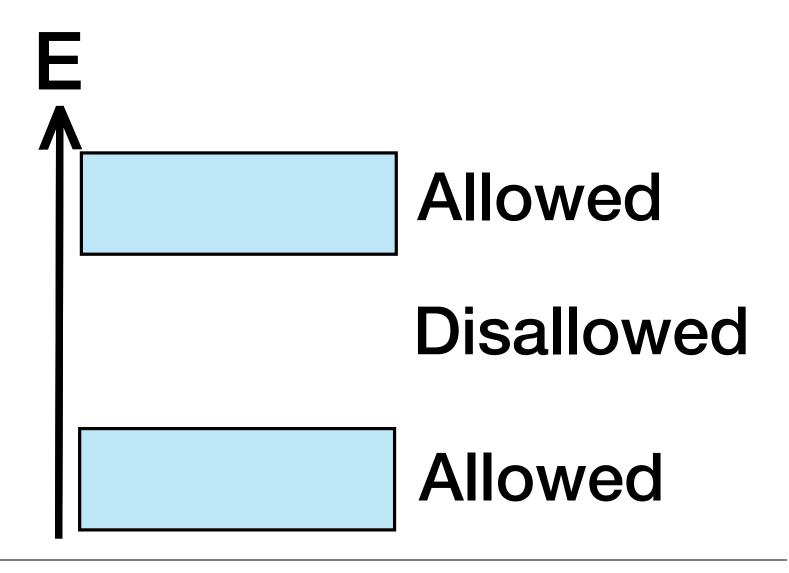














E

CONDUCTION BAND

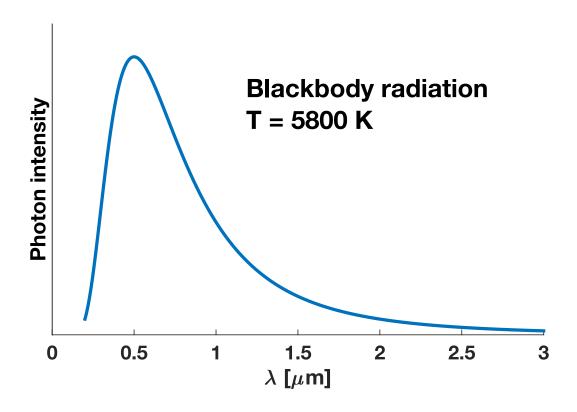
Allowed

Disallowed

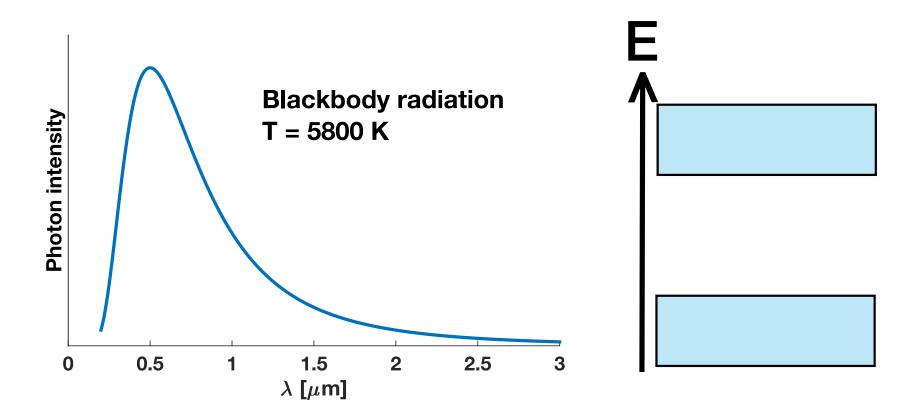
VALENCE BAND

Allowed

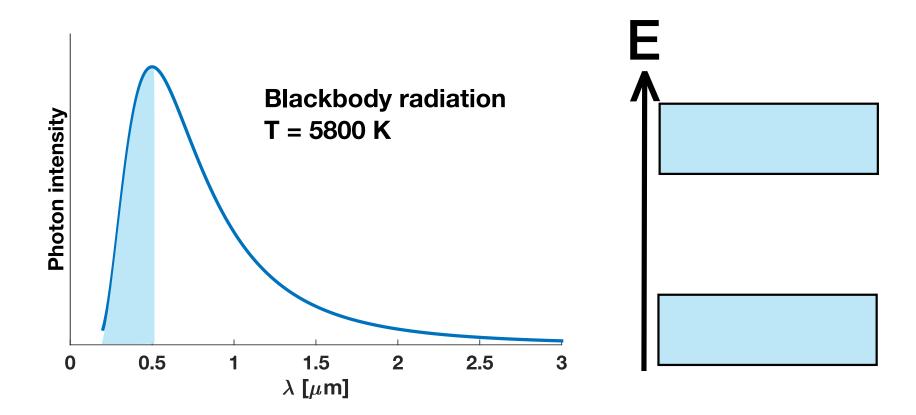




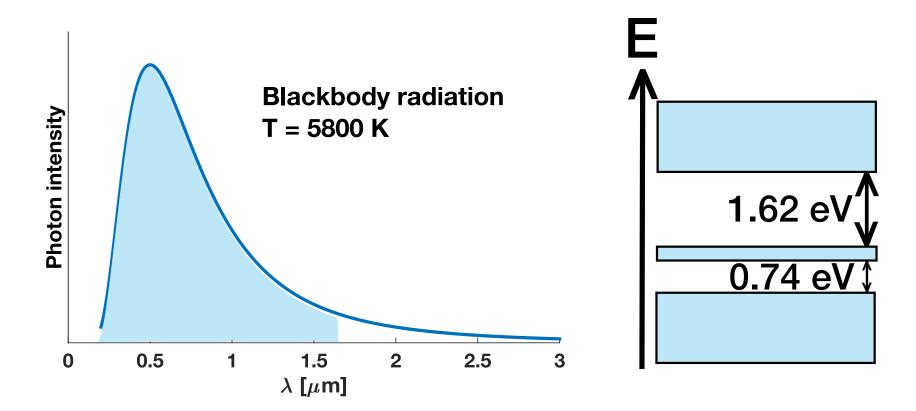














My contributions

Growth of boron-doped samples

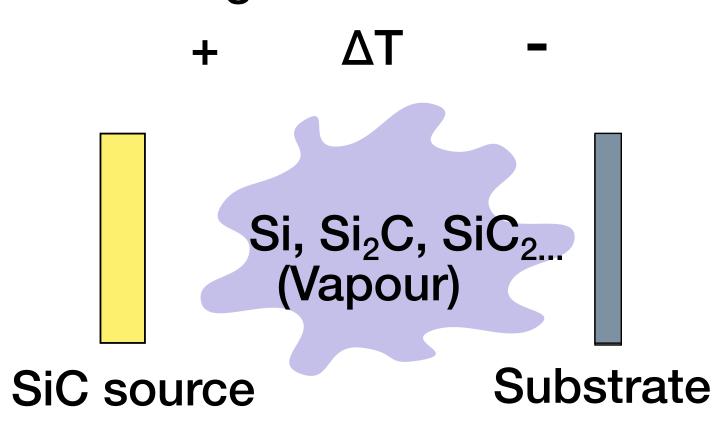


My contributions

- Growth of boron-doped samples
- Optical characterization

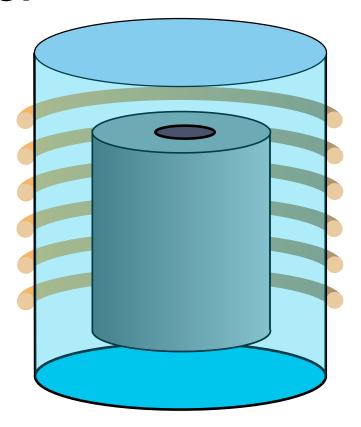


Sublimation growth



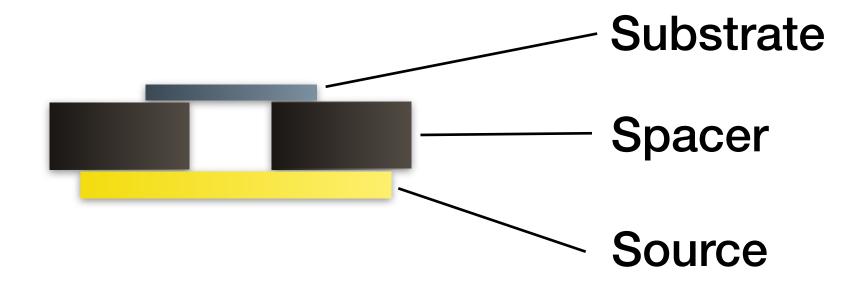


The reactor





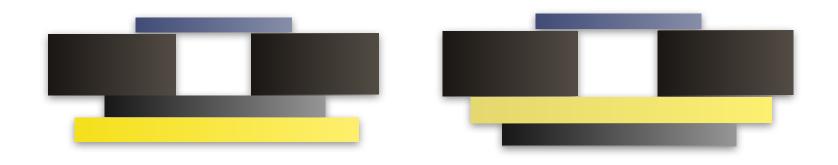
The growth setup





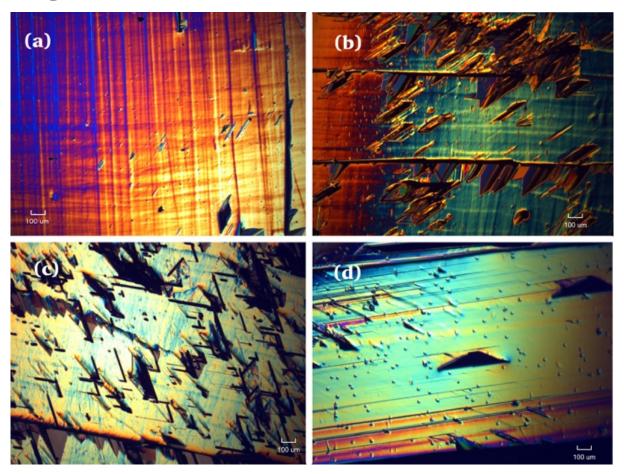
Investigated parameters

- Doping concentrations (10¹⁸ 10²⁰ cm⁻³)
- Growth on 3C seed or 4H substrate
- Direct or indirect doping method



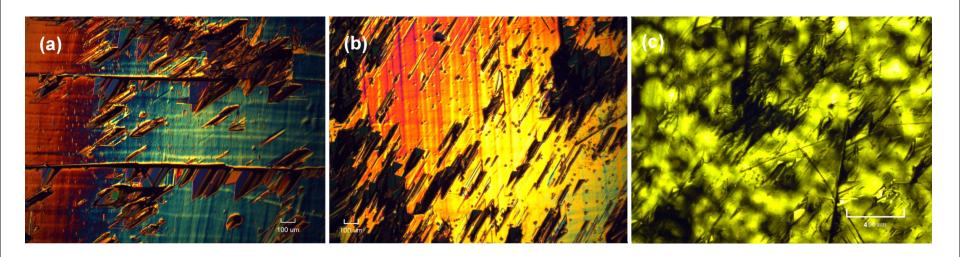


Doping concentrations



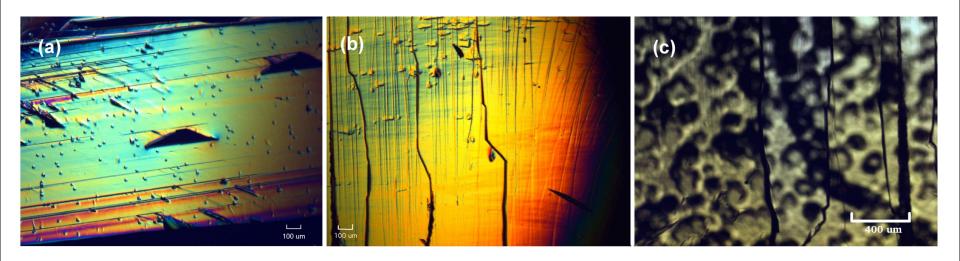


Indirect/direct doping, 10¹⁸ cm⁻³



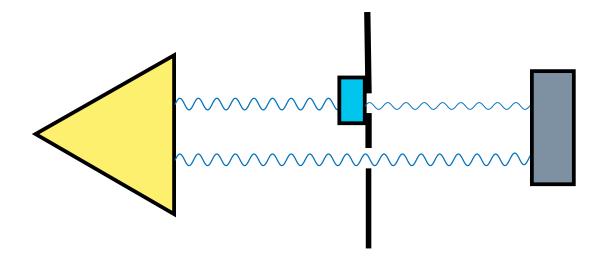


Indirect/direct doping, 10²⁰ cm⁻³

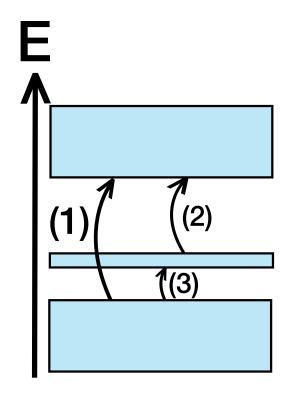




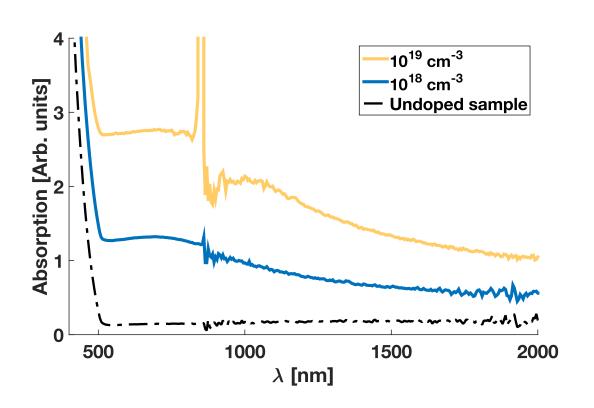


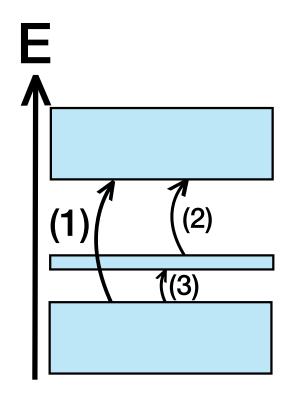




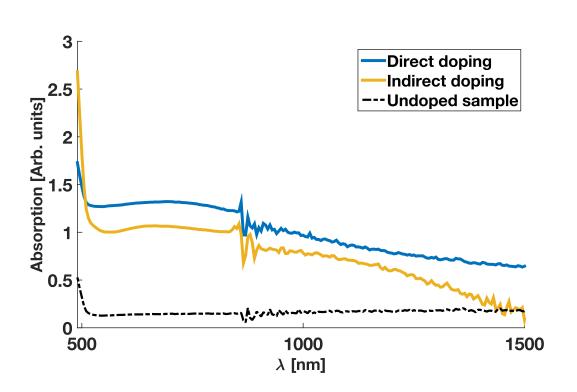


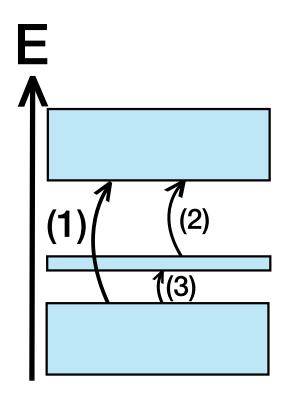




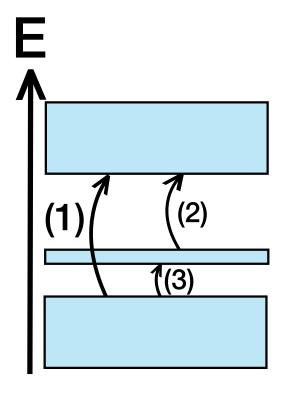




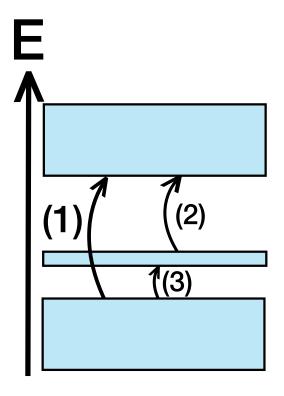






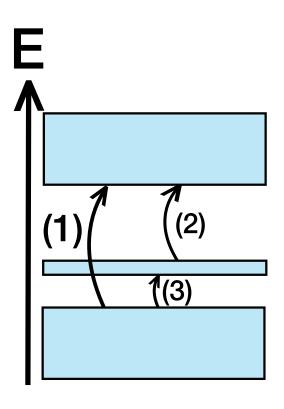






$$p - n = N_A^- - N_D^+$$

$$p - n = N_A^- - N_D^+$$

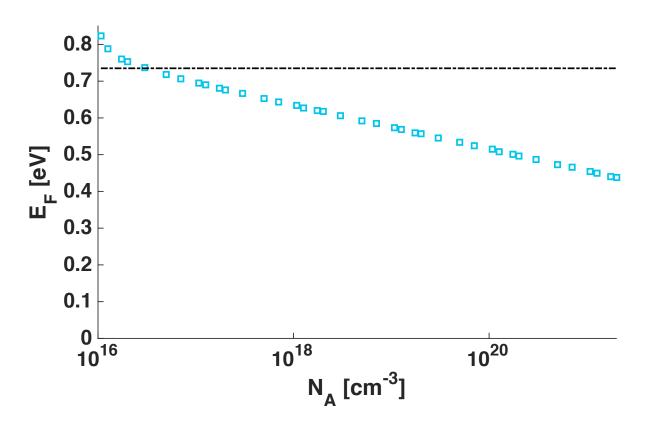


$$N_D^+ \approx N_D$$

$$p \approx N_V e^{-E_F/kT}$$

$$N_A^- = \frac{N_A}{1 + 2e^{\frac{E_A - E_F}{kT}}}$$



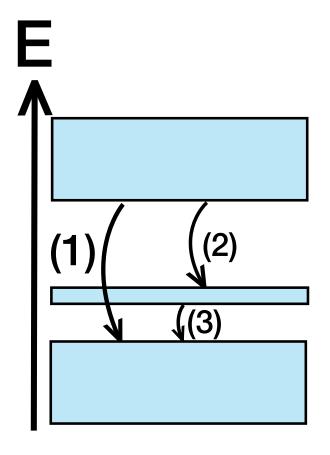




Photoluminescence spectroscopy

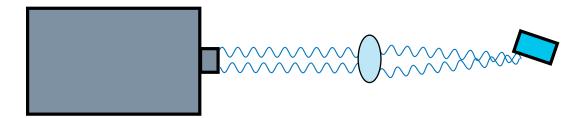


Photoluminescence spectroscopy

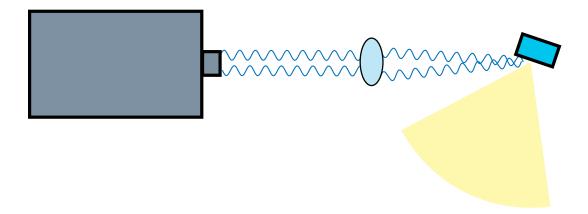




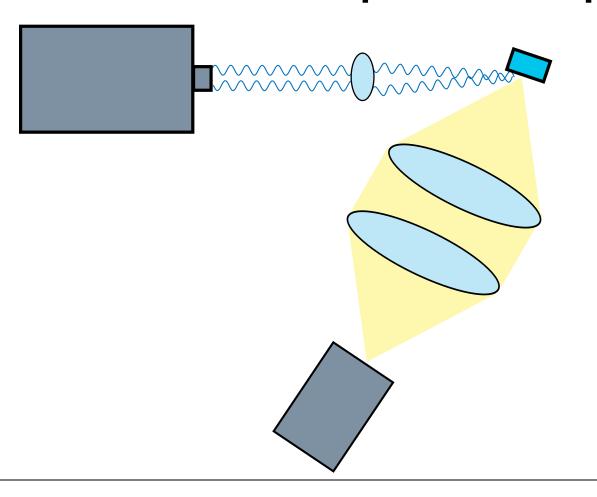
Photoluminescence spectroscopy



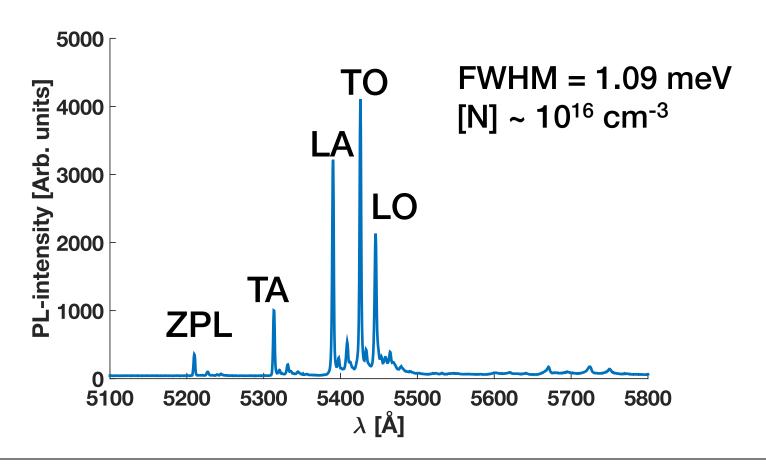




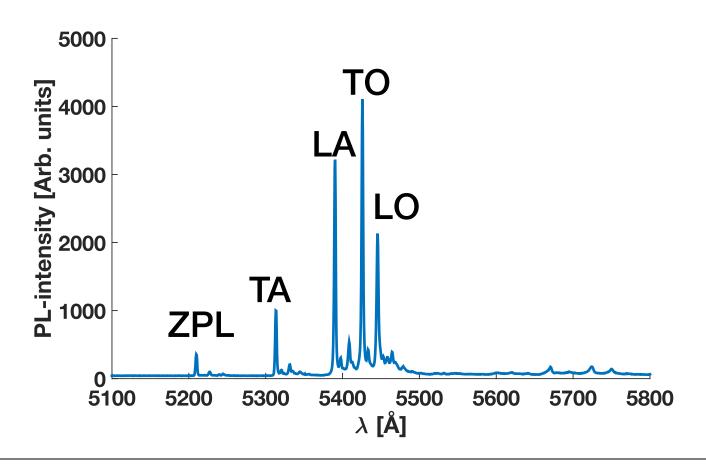




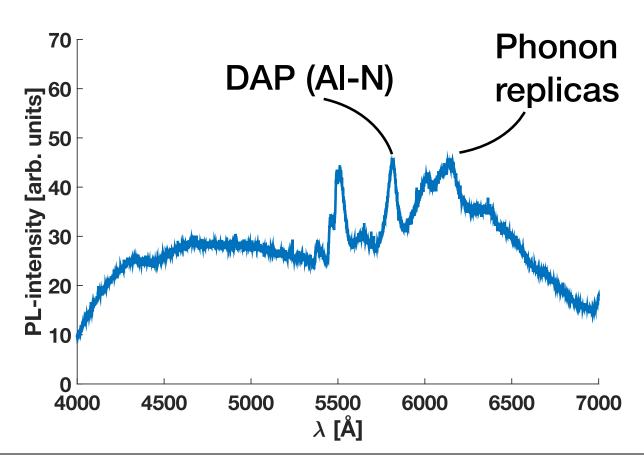




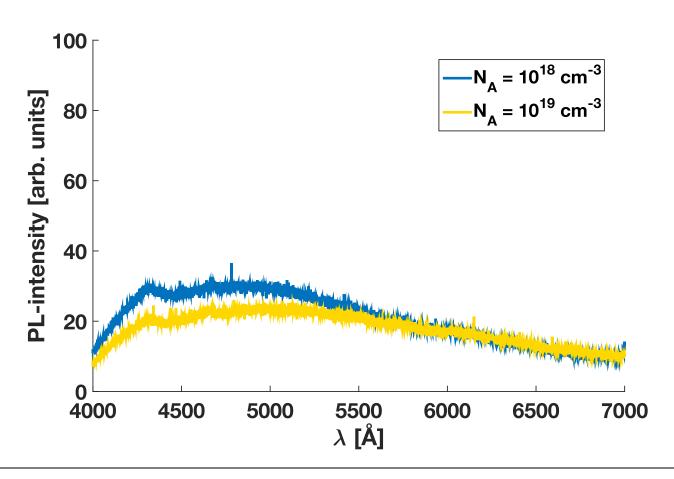




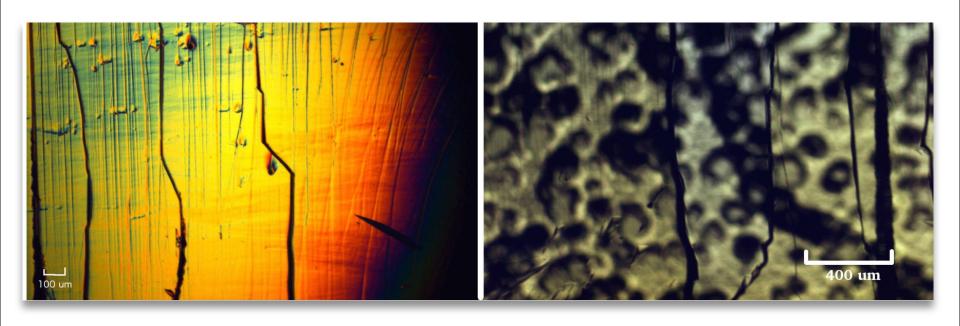














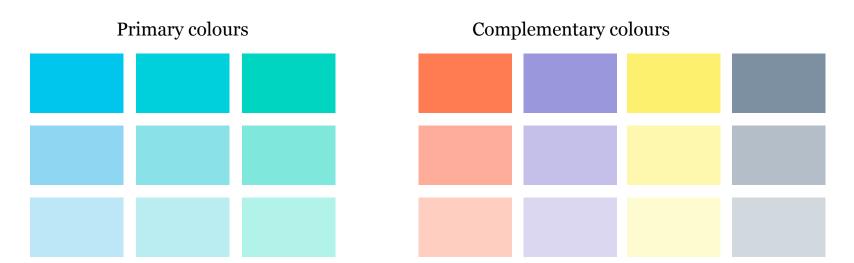
Growth



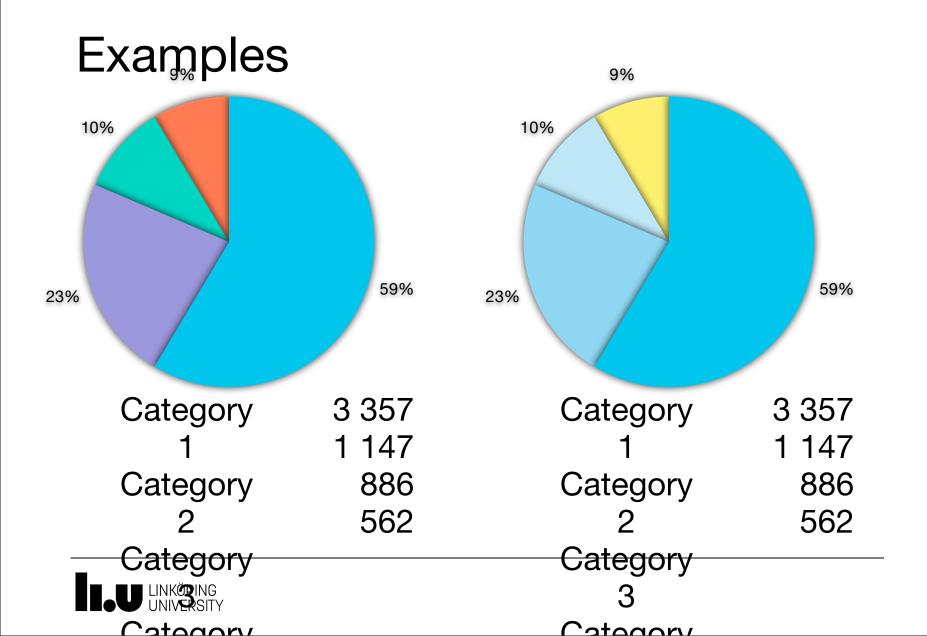
Growth



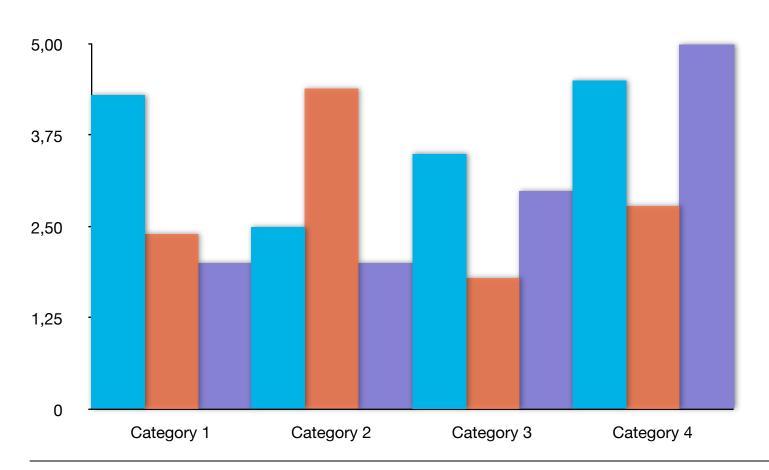
Linköping University's colour chart





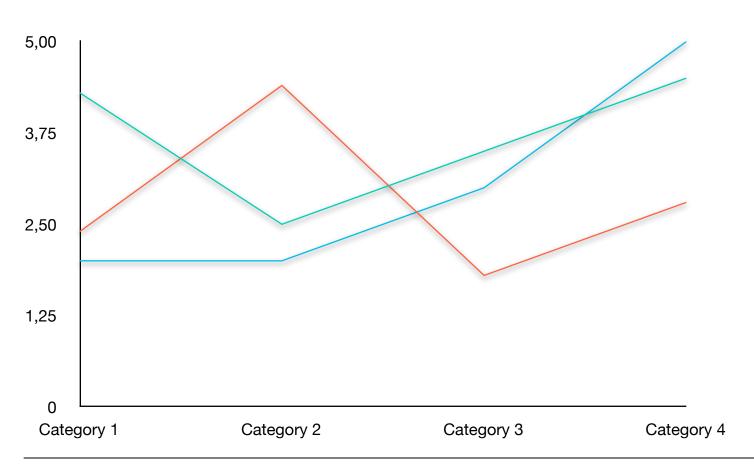


Examples





Examples





www.liu.se

